

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2003-318465

(43)Date of publication of application : 07.11.2003

(51)Int.Cl.

H01L 43/08
H01L 27/105

(21)Application number : 2002-121121

(71)Applicant : NATIONAL INSTITUTE OF
ADVANCED INDUSTRIAL &
TECHNOLOGY
JAPAN SCIENCE & TECHNOLOGY
CORP

(22)Date of filing : 23.04.2002

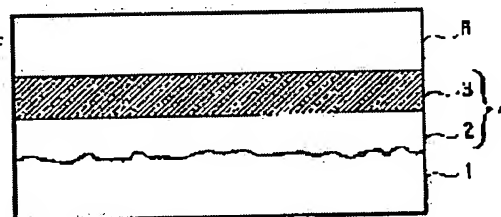
(72)Inventor : YUASA SHINJI
NAGAHAMA TARO
SUZUKI YOSHISHIGE

(54) FLATTENED TUNNEL MAGNETORESISTANCE ELEMENT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a flattened tunnel magnetoresistance element having high alignment and a flat interface without being influenced by the structure and irregularities of a ground such as an amorphous substance and a polycrystalline substance.

SOLUTION: The flattened tunnel magnetoresistance element has a ground layer consisting of double layers of a MgO amorphous layer 2 and a MgO (001) high alignment layer 3.



LEGAL STATUS

[Date of request for examination] 08.05.2002

[Date of sending the examiner's decision of rejection] 04.04.2006

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection] 2006-007890

[Date of requesting appeal against examiner's decision of rejection] 25.04.2006

[Date of extinction of right]